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Remarks:

Claims 20-58 are deemed to be abandoned due to non-payment of the claims fees (Rule 31 (2) EPC).

(54) **Semiconductor light emitting device and method for manufacturing the same**

(57) A nitride-based light emitting device capable of achieving an enhancement in emission efficiency and an enhancement in reliability is disclosed. The light emitting device includes a semiconductor layer, and a light extracting layer arranged on the semiconductor layer and made of a material having a refractive index equal to or higher than a reflective index of the semiconductor layer.

FIG. 3

